





#### P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
-12V	$8.5 \text{m}\Omega$ @ $V_{GS} = -4.5 \text{V}$	-26A
	$12m\Omega @ V_{GS} = -2.5V$	-22A

### **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- ESD Protected up to 8kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

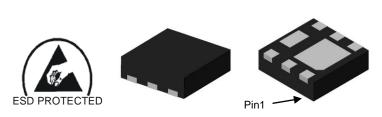
# **Description and Applications**

This MOSFET is designed to minimize on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- Load Switches

### **Mechanical Data**

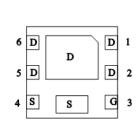
- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.007 grams (Approximate)



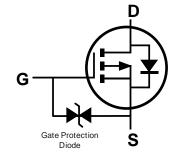
U-DFN2020-6 (Type F)

Top View

Bottom View



Pin Out Bottom View



Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging		
DMP1005UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel		
DMP1005UFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel		

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

# **Marking Information**

U-DFN2020-6 (Type F)



9P = Product Type Marking Code YM = Date Code Marking Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

#### Date Code Key

Year	201	7	2018		2019	20	20	2021		2022		2023
Code	Е		F		G	ŀ	1	I		J		K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	$V_{DSS}$	-12	V		
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Dusin Compant (Nata C) V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-12.8 -10.3	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I <sub>D</sub>	-26 -21	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-70	Α		
Continuous Source-Drain Diode Current (Note 6)	Is	-3.2	Α		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	-20	Α		
Avalanche Energy (Note 7) L = 0.1mH	Eas	20	mJ		

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	0.9	W	
Thormal Basistanas Junation to Ambient (Note 5)	Steady State	D	145	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	92	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	$P_{D}$	2.1	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	59		
Thermal Resistance, Junction to Ambient (Note 0)	t<10s	$R_{\theta JA}$	38	°C/W	
Thermal Resistance, Junction to Case (Note 6)  Steady S		$R_{ heta JC}$	14		
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C	

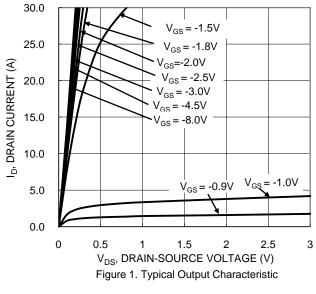
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	-	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-10	μΑ	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	_	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
			5.8	8.5		$V_{GS} = -4.5V, I_{D} = -5A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	7.3	12	mΩ	$V_{GS} = -2.5V, I_D = -4A$	
	` '		9.5	18.5		$V_{GS} = -1.8V, I_D = -2A$	
Diode Forward Voltage	$V_{SD}$	_	-0.8	-1.2	V	$V_{GS} = 0V, I_S = -1.0A$	
DYNAMIC CHARACTERISTICS (Note 9)				·			
Input Capacitance	Ciss	_	2475	_		., ., ., .,	
Output Capacitance	Coss	_	747	_	pF	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		516	_		I = 1.0IVIH2	
Gate Resistance	$R_g$		20	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	28	_			
Total Gate Charge (V <sub>GS</sub> = -8V)	Qg		47	_	0	N	
Gate-Source Charge	Q <sub>gs</sub>	_	3.4	_	nC	$V_{DS} = -6V, I_{D} = -7A$	
Gate-Drain Charge	Q <sub>qd</sub>		7.5	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	6.1	_			
Turn-On Rise Time	t <sub>R</sub>	_	21	_	ns	$V_{DS} = -6V, V_{GS} = -4.5V,$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	140	_		$R_g = 1\Omega$ , $I_D = -7A$	
Turn-Off Fall Time	t <sub>F</sub>	_	125	_		J. Company	
Reverse Recovery Time	t <sub>RR</sub>	_	115	_	ns	I <sub>F</sub> = -1.0A, di/dt = -100A/μs	
Reverse Recovery Charge	Q <sub>RR</sub>	_	75	_	nC	I <sub>F</sub> = -1.0A, di/dt = -100A/μs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

- 7.  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J = +25$ °C.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.





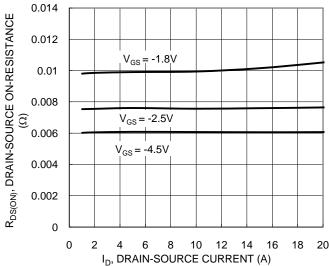


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

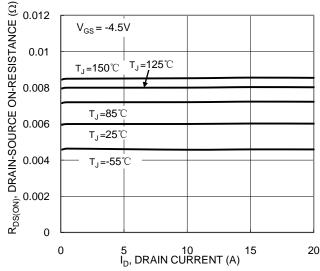
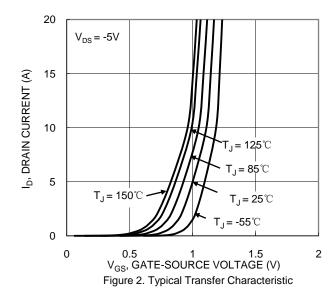
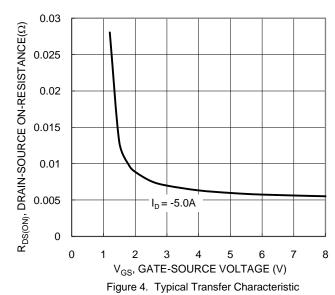


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





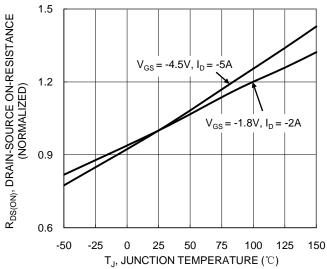
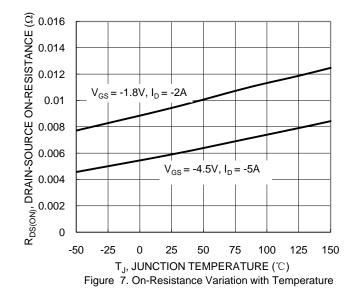
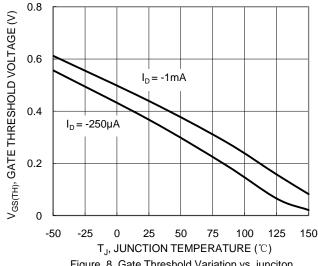
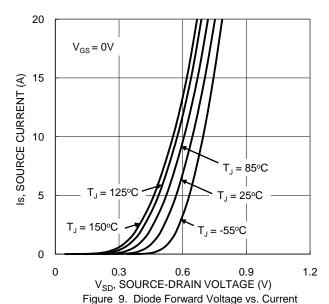


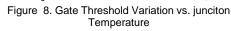
Figure 6. On-Resistance Variation with Temperature

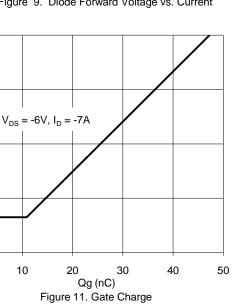


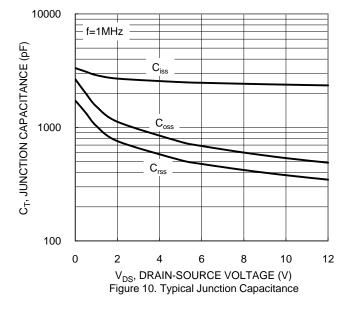


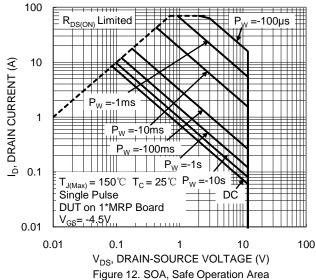












0

10

8

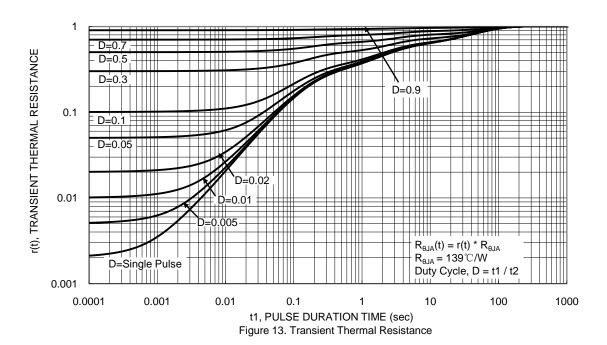
6

2

0

 $V_{GS}(V)$ 



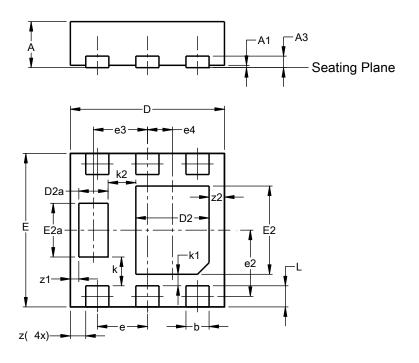




# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

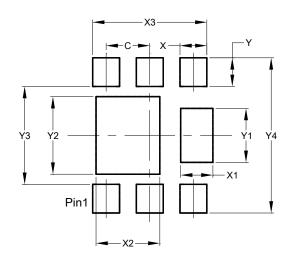


U-DFN2020-6							
(Type F)							
Dim	Min	Max	Тур				
Α	0.57	0.63	0.60				
A1	0.00	0.05	0.03				
A3	-	-	0.15				
b	0.25	0.35	0.30				
D	1.95	2.05	2.00				
D2	0.85	1.05	0.95				
D2a	0.33	0.43	0.38				
Е	1.95	2.05	2.00				
E2	1.05	1.25	1.15				
E2a	0.65	0.75	0.70				
е	0.65 BSC						
e2	0.863 BSC						
е3		0.70 BSC					
e4	0.325 BSC						
k	0.37 BSC						
k1	0.15 BSC						
k2	0.36 BSC						
L	0.225 0.325 0.275						
Z	0.20 BSC						
<b>z</b> 1	0.110 BSC						
z2	0.20 BSC						
All C	All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)



Dimensions	Value
2	(in mm)
C	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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